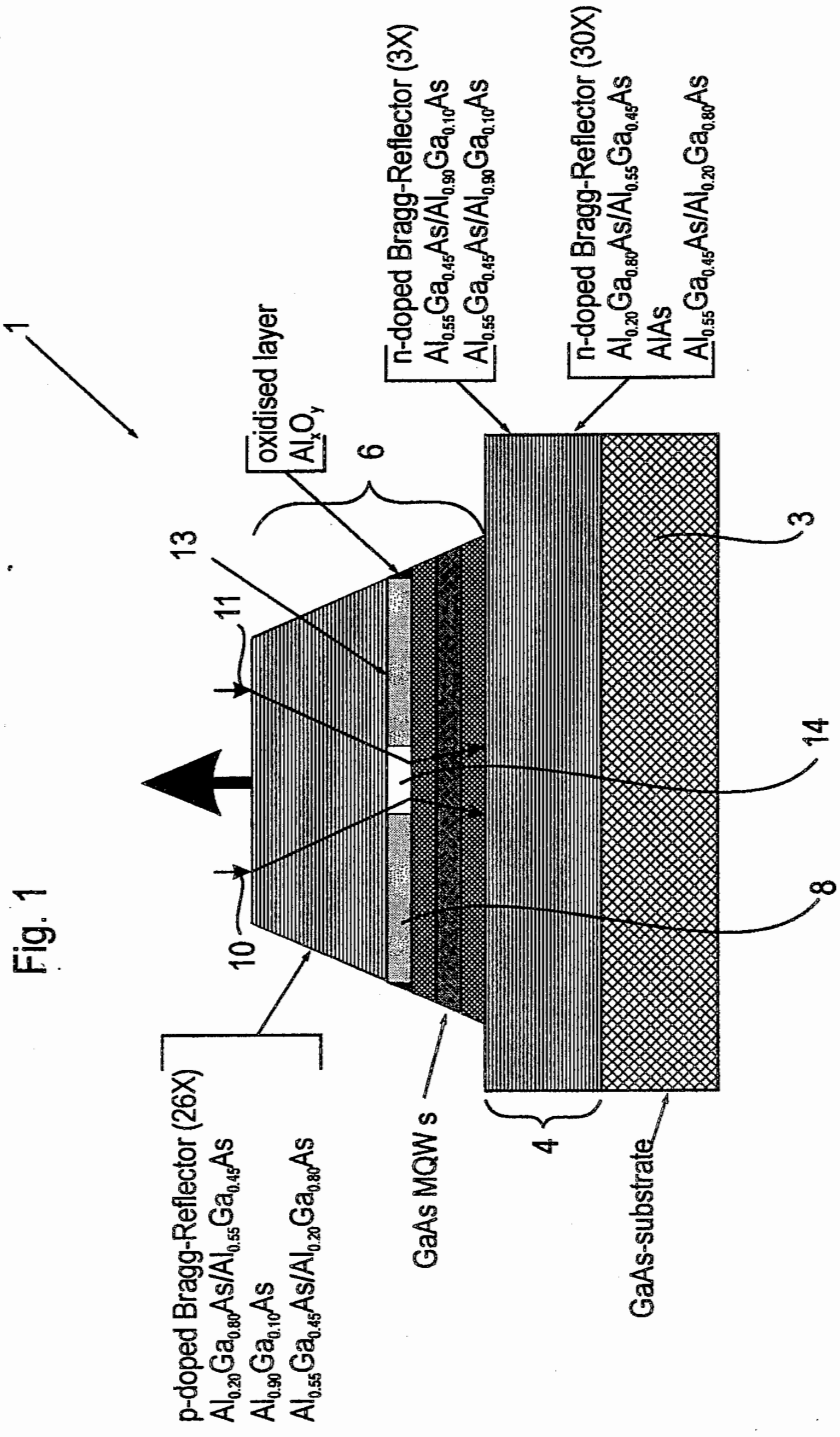
Fig. 1


1
oxidised layer
Al_xO_y
6
n-doped Bragg-Reflector (3X)
$Al_{0.55}Ga_{0.45}As/Al_{0.90}Ga_{0.10}As$
$Al_{0.55}Ga_{0.45}As/Al_{0.90}Ga_{0.10}As$
n-doped Bragg-Reflector (30X)
$Al_{0.20}Ga_{0.80}As/Al_{0.55}Ga_{0.45}As$
Al/As
$Al_{0.55}Ga_{0.45}As/Al_{0.20}Ga_{0.80}As$
13
11
3
14
10
8
p-doped Bragg-Reflector (26X)
$Al_{0.20}Ga_{0.80}As/Al_{0.55}Ga_{0.45}As$
$Al_{0.90}Ga_{0.10}As$
$Al_{0.55}Ga_{0.45}As/Al_{0.20}Ga_{0.80}As$
GaAs MQW s
4
GaAs-substrate

0 5 MAY 2005

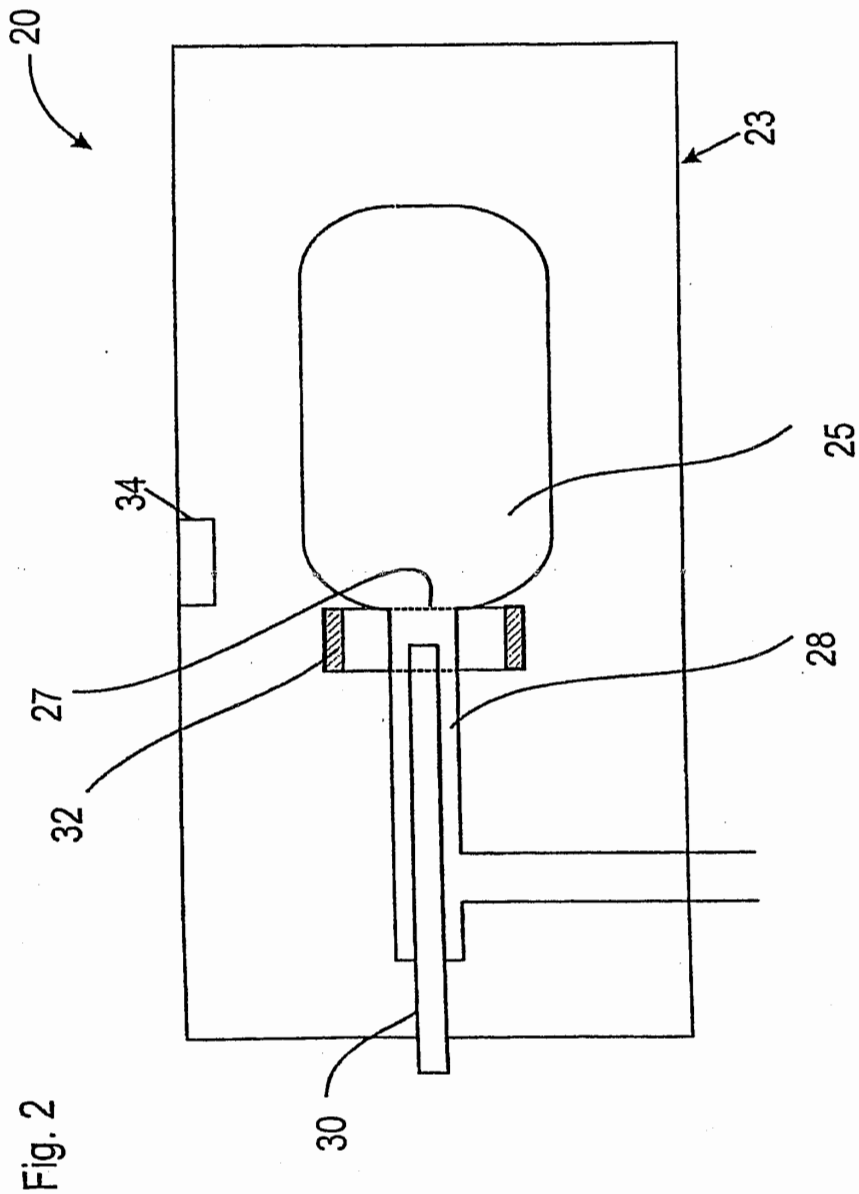


Fig. 2

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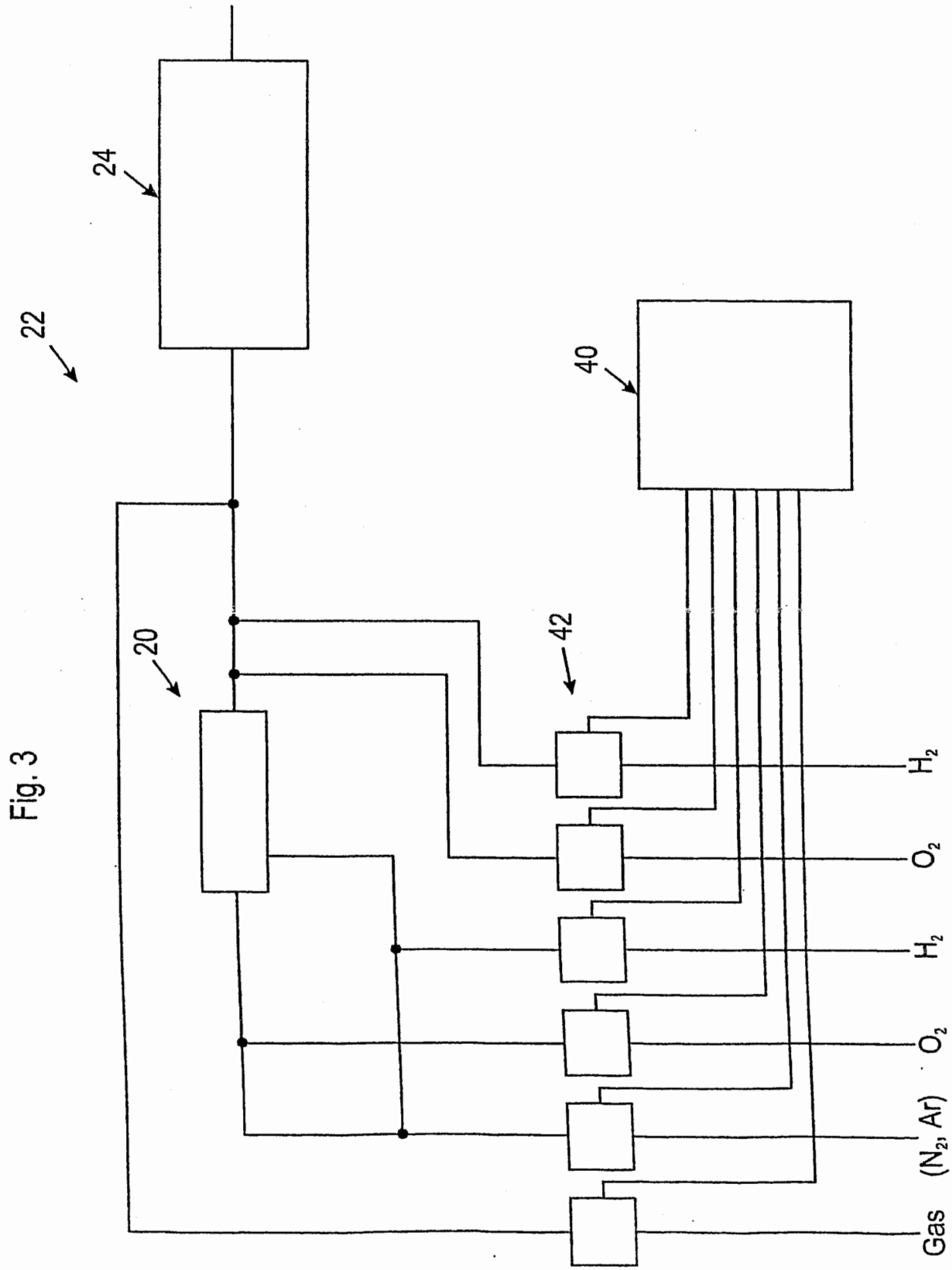


Fig. 3